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November 2015



## MOC3081M, MOC3082M, MOC3083M 6-Pin DIP Zero-Cross Triac Driver Optocoupler (800 Volt Peak)

### Features

- Simplifies Logic Control of 240 VAC Power
- Zero Voltage Crossing to Minimize Conducted and Radiated Line Noise
- 800 V Peak Blocking Voltage
- Superior Static dv/dt
  - 1500 V/µs Typical, 600 V/µs Guaranteed
- Safety and Regulatory Approvals
  - UL1577, 4,170 VAC<sub>RMS</sub> for 1 Minute
  - DIN EN/IEC60747-5-5

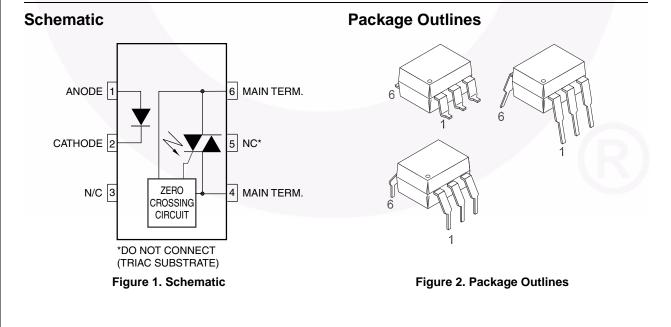
## Applications

- Solenoid/Valve Controls
- Lighting Controls
- Static Power Switches
- AC Motor Starters
- Temperature Controls
- E.M. Contactors
- AC Motor Drives
- Solid State Relays

## Description

The MOC3081M, MOC3082M and MOC3083M devices consist of a GaAs infrared emitting diode optically coupled to a monolithic silicon detector performing the function of a zero voltage crossing bilateral triac driver.

They are designed for use with a discrete power triac in the interface of logic systems to equipment powered from 240 VAC lines, such as solid-state relays, industrial controls, motors, solenoids and consumer appliances, etc.



## Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter		Characteristics
Installation Classifications per DIN VDE	< 150 V <sub>RMS</sub>	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V <sub>RMS</sub>	I–IV
Climatic Classification		40/85/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$ , Type and Sample Test with t <sub>m</sub> = 10 s, Partial Discharge < 5 pC	1360	V <sub>peak</sub>
V <sub>PR</sub>	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$ , 100% Production Test with t <sub>m</sub> = 1 s, Partial Discharge < 5 pC	1594	V <sub>peak</sub>
V <sub>IORM</sub>	Maximum Working Insulation Voltage	850	V <sub>peak</sub>
V <sub>IOTM</sub>	Highest Allowable Over-Voltage	6000	V <sub>peak</sub>
	External Creepage	≥ 7	mm
	External Clearance	≥ 7	mm
	External Clearance (for Option TV, 0.4" Lead Spacing)	≥ 10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.5	mm
R <sub>IO</sub>	Insulation Resistance at T <sub>S</sub> , V <sub>IO</sub> = 500 V	> 10 <sup>9</sup>	Ω

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A = 25^{\circ}C$  unless otherwise specified.

	Parameter	Value	Unit
TOTAL DEV	/ICE		
T <sub>STG</sub>	Storage Temperature	-40 to +150	°C
T <sub>OPR</sub>	Operating Temperature	-40 to +85	°C
TJ	Junction Temperature Range	-40 to +100	°C
T <sub>SOL</sub>	Lead Solder Temperature	260 for 10 seconds	°C
	Total Device Power Dissipation at 25°C Ambient	250	mW
PD	Derate Above 25°C	2.94	mW/°C
EMITTER			
١ <sub>F</sub>	Continuous Forward Current	60	mA
V <sub>R</sub>	Reverse Voltage	6	V
D	Total Power Dissipation at 25°C Ambient	120	mW
PD	Derate Above 25°C	1.41	mW/°C
DETECTOR			
V <sub>DRM</sub>	Off-State Output Terminal Voltage	800	V
I <sub>TSM</sub>	Peak Non-Repetitive Surge Current (Single Cycle 60 Hz Sine Wave)	1	А
Р	Total Power Dissipation at 25°C Ambient	150	mW
PD	Derate Above 25°C	1.76	mW/°C

## **Electrical Characteristics**

 $T_A = 25^{\circ}C$  unless otherwise specified.

#### **Individual Component Characteristics**

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
EMITTER						
V <sub>F</sub>	Input Forward Voltage	I <sub>F</sub> = 30 mA		1.3	1.5	V
I <sub>R</sub>	Reverse Leakage Current	V <sub>R</sub> = 6 V		0.005	100	μA
DETECTO	DR					
I <sub>DRM1</sub>	Peak Blocking Current, Either Direction	V <sub>DRM</sub> = 800 V, I <sub>F</sub> = 0 <sup>(1)</sup>		10	500	nA
dv/dt	Critical Rate of Rise of Off-State Voltage	I <sub>F</sub> = 0 (Figure 11) <sup>(2)</sup>	600	1500		V/µs

#### **Transfer Characteristics**

Symbol	Parameter	Test Conditions	Device	Min.	Тур.	Max.	Unit	
			MOC3081M			15		
I <sub>FT</sub>	LED Trigger Current (Rated I <sub>FT</sub> )	Voltage = 3 V <sup>(6)</sup>		MOC3082M			10	mA
	(Rated I <sub>FT</sub> )		MOC3083M			5		
V <sub>TM</sub>	Peak On-State Voltage, Either Direction	$I_{TM}$ = 100 mA peak, $I_F$ = rated $I_{FT}$	All		1.8	3.0	V	
Ι <sub>Η</sub>	Holding Current, Either Direction		All		500		μA	

#### Zero Crossing Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>INH</sub>	Inhibit Voltage (MT1-MT2 voltage above which device will not trigger)	I <sub>F</sub> = Rated I <sub>FT</sub>		12	20	V
I <sub>DRM2</sub>	Leakage in Inhibited State	I <sub>F</sub> = Rated I <sub>FT</sub> , V <sub>DRM</sub> = 600 V, off-state			2	mA

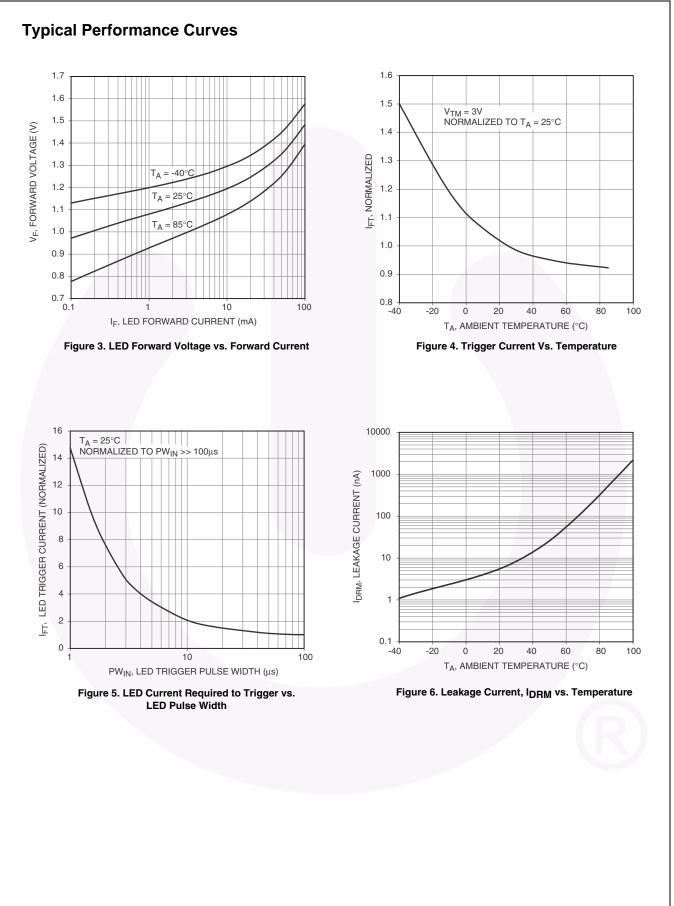
#### **Isolation Characteristics**

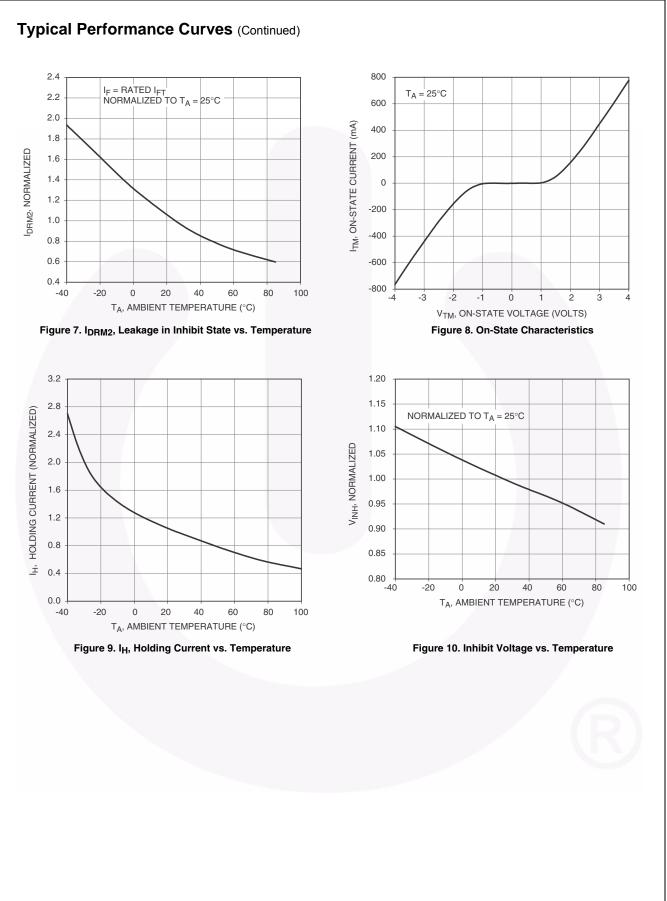
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>ISO</sub>	Isolation Voltage <sup>(4)</sup>	f = 60 Hz, t = 1 Minute	4170			VAC <sub>RMS</sub>
R <sub>ISO</sub>	Isolation Resistance	V <sub>I-O</sub> = 500 V <sub>DC</sub>		10 <sup>11</sup>		Ω
C <sub>ISO</sub>	Isolation Capacitance	V = 0 V, f = 1 MHz		0.2		pF

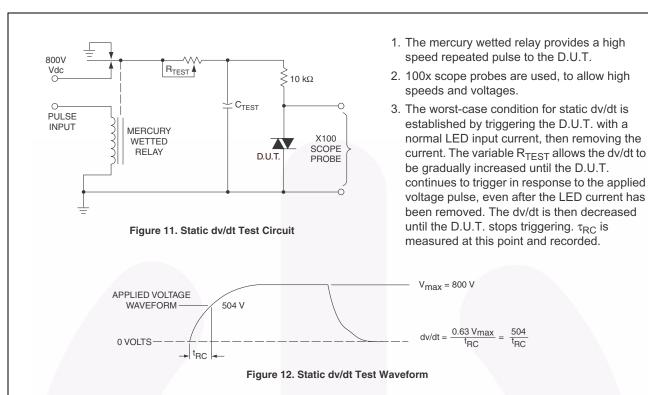
Notes:

1. Test voltage must be applied within dv/dt rating.

- 2. This is static dv/dt. See Figure 11 for test circuit. Commutating dv/dt is a function of the load-driving thyristor(s) only.
- All devices are guaranteed to trigger at an I<sub>F</sub> value less than or equal to max I<sub>FT</sub>. Therefore, recommended operating I<sub>F</sub> lies between max I<sub>FT</sub> (15 mA for MOC3081M, 10 mA for MOC3082M, 5 mA for MOC3083M) and absolute maximum I<sub>F</sub> (60 mA).
- 4. Isolation voltage, V<sub>ISO</sub>, is an internal device dielectric breakdown rating. For this test, pins 1 and 2 are common, and pins 4, 5 and 6 are common.

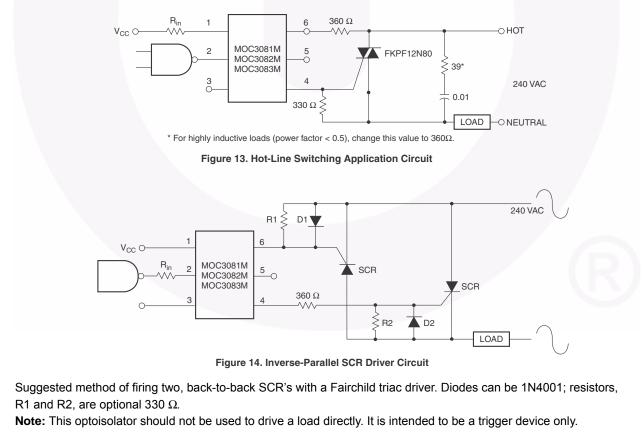


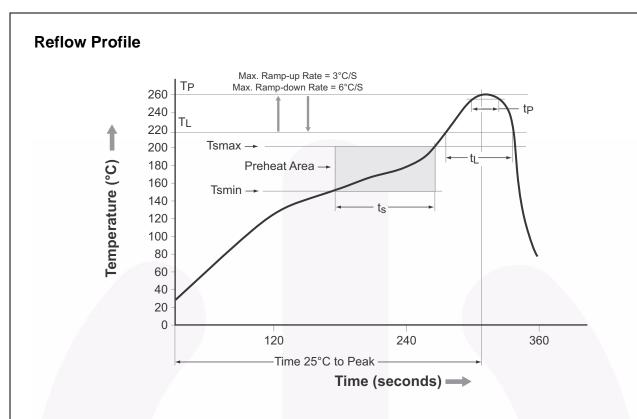




Typical circuit for use when hot line switching is required. In this circuit the "hot" side of the line is switched and the load connected to the cold or neutral side. The load may be connected to either the neutral or hot line.

 $R_{in}$  is calculated so that I<sub>F</sub> is equal to the rated I<sub>FT</sub> of the part, 15 mA for the MOC3081M, 10 mA for the MOC3082M, and 5 mA for the MOC3083M. The 39  $\Omega$  resistor and 0.01  $\mu$ F capacitor are for snubbing of the triac and may or may not be necessary depending upon the particular triac and load use.





Profile Freature	Pb-Free Assembly Profile	
Temperature Minimum (Tsmin)	150°C	
Temperature Maximum (Tsmax)	200°C	
Time (t <sub>S</sub> ) from (Tsmin to Tsmax)	60 seconds to 120 seconds	
Ramp-up Rate (T <sub>L</sub> to T <sub>P</sub> )	3°C/second maximum	
Liquidous Temperature (T <sub>L</sub> )	217°C	
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 seconds to 150 seconds	
Peak Body Package Temperature	260°C +0°C / –5°C	
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds	
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second maximum	
Time 25°C to Peak Temperature	8 minutes maximum	

Figure 15. Reflow Profile

## Ordering Information<sup>(5)</sup>

Part Number	Package	Packing Method
MOC3081M	DIP 6-Pin	Tube (50 Units)
MOC3081SM	SMT 6-Pin (Lead Bend)	Tube (50 Units)
MOC3081SR2M	SMT 6-Pin (Lead Bend)	Tape and Reel (1000 Units)
MOC3081VM	DIP 6-Pin, DIN EN/IEC60747-5-5 Option	Tube (50 Units)
MOC3081SVM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tube (50 Units)
MOC3081SR2VM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tape and Reel (1000 Units)
MOC3081TVM	DIP 6-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 Option	Tube (50 Units)

#### Note:

5. The product orderable part number system listed in this table also applies to the MOC3082M, and MOC3083M, product families.

## **Marking Information**

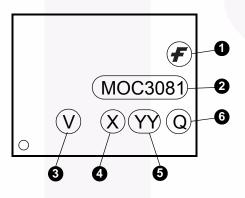
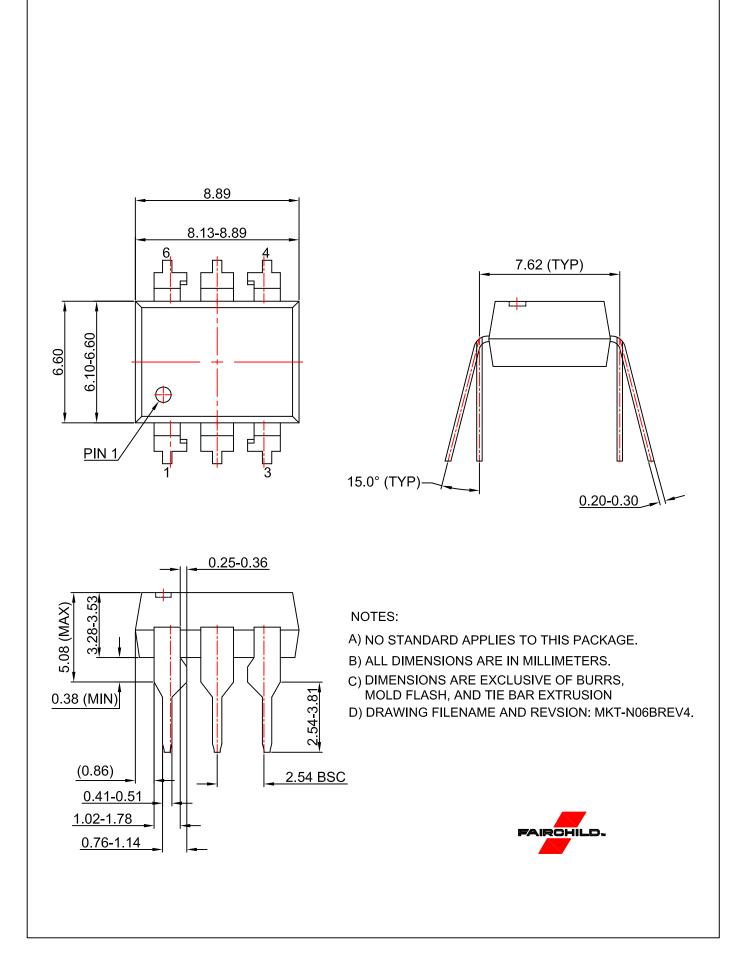
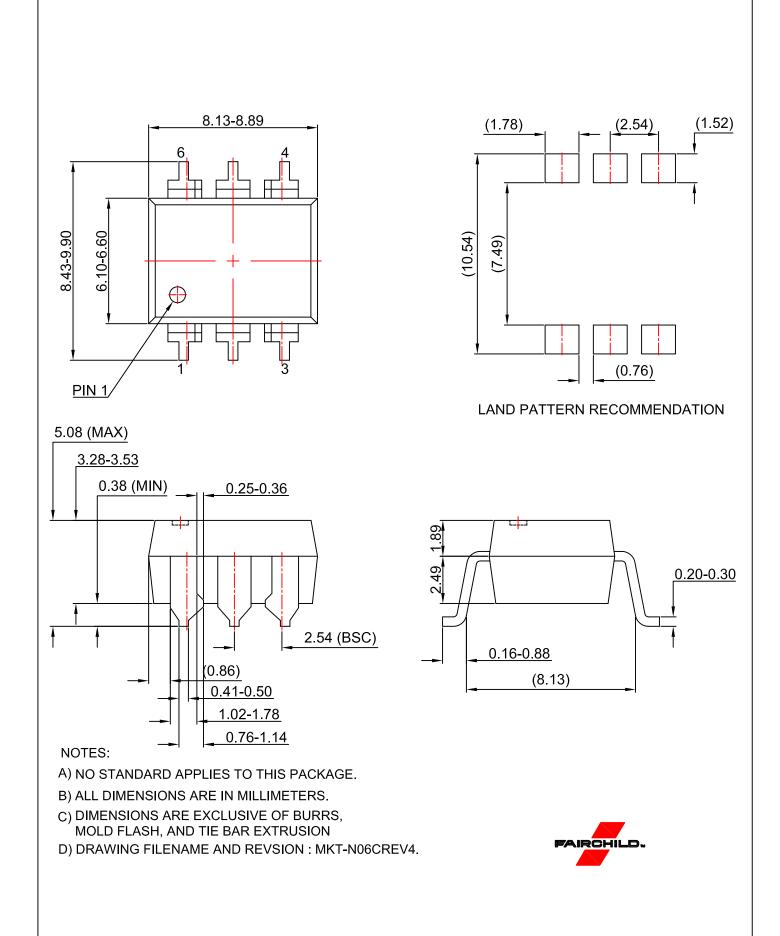
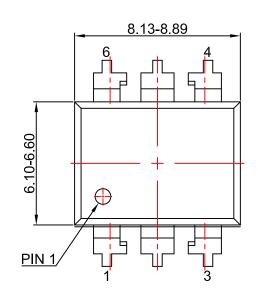


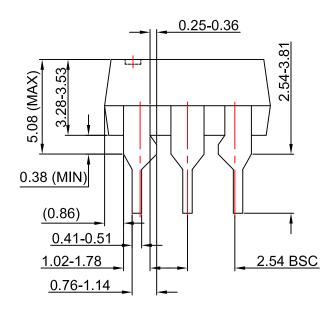
Figure 16. Top Mark

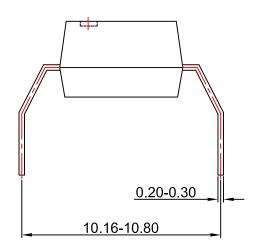
Тор М	Top Mark Definitions			
1	Fairchild Logo			
2	Device Number			
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)			
4	One-Digit Year Code, e.g., '5'			
5	Two-Digit Work Week, Ranging from '01' to '53'			
6	Assembly Package Code			











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